# Motoaki Iwaya

List of Publications by Year
in descending order

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| 154 | 3,630 | 147801 | 168389 |
|---|---|---|---|
| papers | citations | 31 | 53 |
| | | h-index | g-index |

| 155 | 155 | 155 | 2104 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Improved Efficiency of 255â€“280 nm AlGaN-Based Light-Emitting Diodes. Applied Physics Express, 2010, 3, 061004. | 2.4 | 233 |
| 2 | Reduction of Etch Pit Density in Organometallic Vapor Phase Epitaxy-Grown GaN on Sapphire by Insertion of a Low-Temperature-Deposited Buffer Layer between High-Temperature-Grown GaN. Japanese Journal of Applied Physics, 1998, 37, L316-L318. | 1.5 | 184 |
| 3 | 350.9 nm UV Laser Diode Grown on Low-Dislocation-Density AlGaN. Japanese Journal of Applied Physics, 2004, 43, L499-L500. | 1.5 | 151 |
| 4 | Stress and Defect Control in GaN Using Low Temperature Interlayers. Japanese Journal of Applied Physics, 1998, 37, L1540-L1542. | 1.5 | 150 |
| 5 | Solar-Blind UV Photodetectors Based on GaN/AlGaN p-i-n Photodiodes. Japanese Journal of Applied Physics, 2000, 39, L387-L389. | 1.5 | 108 |
| 6 | Epitaxial lateral overgrowth of AlN on trench-patterned AlN layers. Journal of Crystal Growth, 2007, 298, 257-260. | 1.5 | 104 |
| 7 | High-Temperature Metal-Organic Vapor Phase Epitaxial Growth of AlN on Sapphire by Multi Transition Growth Mode Method Varying V/III Ratio. Japanese Journal of Applied Physics, 2006, 45, 8639-8643. | 1.5 | 101 |
| 8 | Dislocations in AlN Epilayers Grown on Sapphire Substrate by High-Temperature Metal-Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2007, 46, 1458-1462. | 1.5 | 90 |
| 9 | Low-temperature-deposited AlGaN interlayer for improvement of AlGaN/GaN heterostructure. Journal of Crystal Growth, 2001, 223, 83-91. | 1.5 | 82 |
| 10 | Room-temperature continuous-wave operation of GaN-based vertical-cavity surface-emitting lasers with n-type conducting AlInN/GaN distributed Bragg reflectors. Applied Physics Express, 2016, 9, 102101. | 2.4 | 78 |
| 11 | Annihilation mechanism of threading dislocations in AlN grown by growth form modification method using V/III ratio. Journal of Crystal Growth, 2007, 300, 136-140. | 1.5 | 66 |
| 12 | Impact of high-temperature growth by metal-organic vapor phase epitaxy on microstructure of AlN on 6H-SiC substrates. Journal of Crystal Growth, 2008, 310, 2308-2313. | 1.5 | 65 |
| 13 | Control of crystallinity of GaN grown on sapphire substrate by metalorganic vapor phase epitaxy using in situ X-ray diffraction monitoring method. Journal of Crystal Growth, 2014, 401, 367-371. | 1.5 | 60 |
| 14 | Realization of crack-free and high-quality thick AlxGa1â^'xN for UV optoelectronics using low-temperature interlayer. Applied Surface Science, 2000, 159-160, 405-413. | 6.1 | 56 |
| 15 | Novel UV devices on high-quality AlGaN using grooved underlying layer. Journal of Crystal Growth, 2009, 311, 2860-2863. | 1.5 | 55 |
| 16 | High-efficiency AlGaN-based UV light-emitting diode on laterally overgrown AlN. Journal of Crystal Growth, 2008, 310, 2326-2329. | 1.5 | 54 |
| 17 | Realization of Nitride-Based Solar Cell on Freestanding GaN Substrate. Applied Physics Express, 2010, 3, 111001. | 2.4 | 52 |
| 18 | Improvement of Light Extraction Efficiency for AlGaN-Based Deep Ultraviolet Light-Emitting Diodes. Japanese Journal of Applied Physics, 2011, 50, 122101. | 1.5 | 52 |

| # | Article | IF | Citations |
|---|---|---|---|
| 19 | GaInN-Based Tunnel Junctions in nâ€“pâ€“n Light Emitting Diodes. Japanese Journal of Applied Physics, 2013, 52, 08JH06. | 1.5 | 51 |
| 20 | Low-Intensity Ultraviolet Photodetectors Based on AlGaN. Japanese Journal of Applied Physics, 1999, 38, L487-L489. | 1.5 | 45 |
| 21 | Influence of High Temperature in the Growth of Low Dislocation Content AlN Bridge Layers on Patterned 6H-SiC Substrates by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2007, 46, L307-L310. | 1.5 | 45 |
| 22 | Flat (11ar20) GaN Thin Film on Precisely Offset-Controlled (1ar102) Sapphire Substrate. Japanese Journal of Applied Physics, 2005, 44, 7418-7420. | 1.5 | 44 |
| 23 | Control of p-Type Conduction in a-Plane GaN Grown on Sapphire r-Plane Substrate. Japanese Journal of Applied Physics, 2005, 44, L1516-L1518. | 1.5 | 44 |
| 24 | Highâ€performance UV emitter grown on highâ€crystallineâ€quality AlGaN underlying layer. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1199-1204. | 1.8 | 41 |
| 25 | High-Efficiency Nitride-Based Light-Emitting Diodes with Moth-Eye Structure. Japanese Journal of Applied Physics, 2005, 44, 7414-7417. | 1.5 | 39 |
| 26 | High-performance solar-blind Al0.6Ga0.4N/Al0.5Ga0.5N MSM type photodetector. Applied Physics Letters, 2017, 111, . | 3.3 | 39 |
| 27 | Ultraviolet-B band lasers fabricated on highly relaxed thick Al<sub>0.55</sub>Ga<sub>0.45</sub>N films grown on various types of AlN wafers. Japanese Journal of Applied Physics, 2019, 58, SC1052. | 1.5 | 36 |
| 28 | AlGaN-based UV-B laser diode with a high optical confinement factor. Applied Physics Letters, 2021, 118, . | 3.3 | 36 |
| 29 | Microscopic Investigation of Al0.43Ga0.57N on Sapphire. Japanese Journal of Applied Physics, 1999, 38, L1515-L1518. | 1.5 | 33 |
| 30 | Fracture of AlxGa1-xN/GaN Heterostructure -- Compositional and Impurity Dependence --. Japanese Journal of Applied Physics, 2001, 40, L195-L197. | 1.5 | 33 |
| 31 | Laser diode of 350.9nm wavelength grown on sapphire substrate by MOVPE. Journal of Crystal Growth, 2004, 272, 270-273. | 1.5 | 33 |
| 32 | Light confinement and high current density in UVB laser diode structure using Al composition-graded p-AlGaN cladding layer. Applied Physics Letters, 2019, 114, . | 3.3 | 33 |
| 33 | One-sidewall-seeded epitaxial lateral overgrowth of a-plane GaN by metalorganic vapor-phase epitaxy. Journal of Crystal Growth, 2009, 311, 2887-2890. | 1.5 | 31 |
| 34 | Development of AlN/diamond heterojunction field effect transistors. Diamond and Related Materials, 2012, 24, 206-209. | 3.9 | 31 |
| 35 | Low-Leakage-Current Enhancement-Mode AlGaN/GaN Heterostructure Field-Effect Transistor Using p-Type Gate Contact. Japanese Journal of Applied Physics, 2006, 45, L319-L321. | 1.5 | 30 |
| 36 | Compensation effect of Mg-doped a- and c-plane GaN films grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2010, 312, 3131-3135. | 1.5 | 30 |

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| 37 | Growth of Highâ€Quality AlN and AlGaN Films on Sputtered AlN/Sapphire Templates via Highâ€Temperature Annealing. Physica Status Solidi (B): Basic Research, 2018, 255, 1700506. | 1.5 | 30 |
| 38 | High-Power UV-Light-Emitting Diode on Sapphire. Japanese Journal of Applied Physics, 2003, 42, 400-403. | 1.5 | 29 |
| 39 | Control of Threshold Voltage of Enhancement-Mode AlxGa1-xN/GaN Junction Heterostructure Field-Effect Transistors Using p-GaN Gate Contact. Japanese Journal of Applied Physics, 2007, 46, 115-118. | 1.5 | 28 |
| 40 | Extremely Low-Resistivity and High-Carrier-Concentration Si-Doped Al<sub>0.05</sub>Ga<sub>0.95</sub>N. Applied Physics Express, 2013, 6, 121002. | 2.4 | 27 |
| 41 | GaInNâ€based tunnel junctions with high InN mole fractions grown by MOVPE. Physica Status Solidi (B): Basic Research, 2015, 252, 1127-1131. | 1.5 | 27 |
| 42 | GaInN-based tunnel junctions with graded layers. Applied Physics Express, 2016, 9, 081005. | 2.4 | 27 |
| 43 | Thermodynamic Aspects of Growth of AlGaN by High-Temperature Metal Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2006, 45, 2502-2504. | 1.5 | 26 |
| 44 | High On/Off Ratio in Enhancement-Mode AlxGa1-xN/GaN Junction Heterostructure Field-Effect Transistors with P-Type GaN Gate Contact. Japanese Journal of Applied Physics, 2006, 45, L1048-L1050. | 1.5 | 25 |
| 45 | High-quality AlN film grown on a nanosized concaveâ€“convex surface sapphire substrate by metalorganic vapor phase epitaxy. Applied Physics Letters, 2017, 111, . | 3.3 | 23 |
| 46 | 450Ânm GaInN ridge stripe laser diodes with AlInN/AlGaN multiple cladding layers. Japanese Journal of Applied Physics, 2019, 58, SCCC28. | 1.5 | 23 |
| 47 | Effect of AlGaN undershell on the cathodoluminescence properties of coaxial GaInN/GaN multiple-quantum-shells nanowires. Nanoscale, 2019, 11, 18746-18757. | 5.6 | 23 |
| 48 | Anisotropically Biaxial Strain ina-Plane AlGaN on GaN Grown onr-Plane Sapphire. Japanese Journal of Applied Physics, 2006, 45, 2509-2513. | 1.5 | 22 |
| 49 | White light-emitting diode based on fluorescent SiC. Thin Solid Films, 2012, 522, 23-25. | 1.8 | 21 |
| 50 | The dependence of AlN molar fraction of AlGaN in wet etching by using tetramethylammonium hydroxide aqueous solution. Japanese Journal of Applied Physics, 2019, 58, SCCC30. | 1.5 | 21 |
| 51 | Determination of internal quantum efficiency in GaInN-based light-emitting diode under electrical injection: carrier recombination dynamics analysis. Applied Physics Express, 2019, 12, 032006. | 2.4 | 21 |
| 52 | Growth and Characterization of Core-Shell Structures Consisting of GaN Nanowire Core and GaInN/GaN Multi-Quantum Shell. ECS Journal of Solid State Science and Technology, 2020, 9, 015007. | 1.8 | 21 |
| 53 | Strain Relaxation Mechanisms in AlGaN Epitaxy on AlN Templates. Applied Physics Express, 2010, 3, 111003. | 2.4 | 20 |
| 54 | Analysis of strain relaxation process in GaInN/GaN heterostructure by in situ Xâ€ray diffraction monitoring during metalorganic vaporâ€phase epitaxial growth. Physica Status Solidi - Rapid Research Letters, 2013, 7, 211-214. | 2.4 | 20 |

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| 55 | Photoresponse and Defect Levels of AlGaN/GaN Heterobipolar Phototransistor Grown on Low-Temperature AlN Interlayer. Japanese Journal of Applied Physics, 2001, 40, L498-L501. | 1.5 | 18 |
| 56 | Epitaxial lateral overgrowth of AlxGa1â^'xN (x>0.2) on sapphire and its application to UV-B-light-emitting devices. Journal of Crystal Growth, 2007, 298, 265-267. | 1.5 | 18 |
| 57 | Relationship between misfit-dislocation formation and initial threading-dislocation density in GaInN/GaN heterostructures. Japanese Journal of Applied Physics, 2015, 54, 115501. | 1.5 | 16 |
| 58 | High Crystallinity and Highly Relaxed Al<sub>0.60</sub>Ga<sub>0.40</sub>N Films Using Growth Mode Control Fabricated on a Sputtered AlN Template with Highâ€Temperature Annealing. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900868. | 1.8 | 16 |
| 59 | Reduction of dislocation density in lattice-relaxed Al<sub>0.68</sub>Ga<sub>0.32</sub>N film grown on periodical 1 Î¼m spacing AlN pillar concave-convex patterns and its effect on the performance of UV-B laser diodes. Applied Physics Express, 2022, 15, 031004. | 2.4 | 16 |
| 60 | Realization of low-dislocation-density, smooth surface, and thick GaInN films on m-plane GaN templates. Journal of Crystal Growth, 2008, 310, 3308-3312. | 1.5 | 15 |
| 61 | GaN-based vertical-cavity surface-emitting lasers using n-type conductive AlInN/GaN bottom distributed Bragg reflectors with graded interfaces. Japanese Journal of Applied Physics, 2019, 58, SCCC01. | 1.5 | 15 |
| 62 | Improved Uniform Current Injection into Coreâ€Shellâ€Type GaInN Nanowire Lightâ€Emitting Diodes by Optimizing Growth Condition and Indiumâ€Tinâ€Oxide Deposition. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900715. | 1.8 | 15 |
| 63 | Controlled synthesis of nonpolar GaInN/GaN multiple-quantum-shells on GaN nanowires by metal-organic chemical vapour deposition. Applied Surface Science, 2020, 509, 145271. | 6.1 | 15 |
| 64 | Realization of High-Crystalline-Quality Thick m-Plane GaInN Film on 6H-SiC Substrate by Epitaxial Lateral Overgrowth. Japanese Journal of Applied Physics, 2007, 46, L948. | 1.5 | 14 |
| 65 | High hole concentration in Mg-doped a-plane Ga1â^'xInxNâ€^(<x<0.30) grown on r-plane sapphire substrate by metalorganic vapor phase epitaxy. Applied Physics Letters, 2008, 93, . | 3.3 | 14 |
| 66 | Injection efficiency in AlGaNâ€based UV laser diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2384-2386. | 0.8 | 14 |
| 67 | Characterization and optimization of sputtered AlN buffer layer on r-plane sapphire substrate to improve the crystalline quality of nonpolar a-plane GaN. Journal of Crystal Growth, 2017, 480, 90-95. | 1.5 | 14 |
| 68 | Hybrid simulation of light extraction efficiency in multi-quantum-shell (MQS) NW (nanowire) LED with a current diffusion layer. Japanese Journal of Applied Physics, 2019, 58, SCCC17. | 1.5 | 14 |
| 69 | Low-threshold-current (~85 mA) of AlGaN-based UV-B laser diode with refractive-index waveguide structure. Applied Physics Express, 2021, 14, 094009. | 2.4 | 14 |
| 70 | n-type GaN surface etched green light-emitting diode to reduce non-radiative recombination centers. Applied Physics Letters, 2021, 118, . | 3.3 | 14 |
| 71 | Identification of multi-color emission from coaxial GaInN/GaN multiple-quantum-shell nanowire LEDs. Nanoscale Advances, 2021, 4, 102-110. | 4.6 | 14 |
| 72 | Reduction in threshold current density of 355 nm UV laser diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1564-1568. | 0.8 | 13 |

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| 73 | Modified Shockley Equation for GaInN-Based Light-Emitting Diodes: Origin of the Power- Efficiency Degradation Under High Current Injection. IEEE Journal of Quantum Electronics, 2019, 55, 1-11. | 1.9 | 13 |
| 74 | Development of Monolithically Grown Coaxial GaInN/GaN Multiple Quantum Shell Nanowires by MOCVD. Nanomaterials, 2020, 10, 1354. | 4.1 | 13 |
| 75 | Recent development of UV-B laser diodes. Japanese Journal of Applied Physics, 2022, 61, 040501. | 1.5 | 13 |
| 76 | X-ray diffraction reciprocal lattice space mapping ofa-plane AlGaN on GaN. Physica Status Solidi (B): Basic Research, 2006, 243, 1524-1528. | 1.5 | 12 |
| 77 | Relaxation and recovery processes of AlxGa1â^'xN grown on AlN underlying layer. Journal of Crystal Growth, 2009, 311, 2850-2852. | 1.5 | 12 |
| 78 | Fabrication of Nonpolar $a$-Plane Nitride-Based Solar Cell on $r$-Plane Sapphire Substrate. Applied Physics Express, 2011, 4, 101001. | 2.4 | 12 |
| 79 | Properties of nitrideâ€based photovoltaic cells under concentrated light illumination. Physica Status Solidi - Rapid Research Letters, 2012, 6, 145-147. | 2.4 | 12 |
| 80 | Sapphire substrate off-angle and off-direction dependences on characteristics of AlGaN-based deep ultraviolet light-emitting diodes. Japanese Journal of Applied Physics, 2019, 58, SC1025. | 1.5 | 12 |
| 81 | Analysis of Spontaneous Subpeak Emission from the Guide Layers of the Ultravioletâ€B Laser Diode Structure Containing Compositionâ€Graded pâ€AlGaN Cladding Layers. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900864. | 1.8 | 12 |
| 82 | GaN-based vertical cavity surface emitting lasers with lateral optical confinements and conducting distributed Bragg reflectors. Japanese Journal of Applied Physics, 2020, 59, SGGE08. | 1.5 | 12 |
| 83 | Reduction of dislocation density in Al0.6Ga0.4N film grown on sapphire substrates using annealed sputtered AlN templates and its effect on UV-B laser diodes. Journal of Crystal Growth, 2021, 575, 126325. | 1.5 | 12 |
| 84 | Room-temperature continuous-wave operations of GaN-based vertical-cavity surface-emitting lasers with buried GaInN tunnel junctions. Applied Physics Express, 2020, 13, 111003. | 2.4 | 12 |
| 85 | High-quality AlInN/GaN distributed Bragg reflectors grown by metalorganic vapor phase epitaxy. Applied Physics Express, 2020, 13, 125504. | 2.4 | 12 |
| 86 | Improvement of 650-nm red-emitting GaIn0.17N/GaIn0.38N multiple quantum wells on ScAlMgO4 (0001) substrate by suppressing impurity diffusion/penetration. Applied Physics Letters, 2022, 120, . | 3.3 | 12 |
| 87 | High-quality Al0.12Ga0.88N film with low dislocation density grown on facet-controlled Al0.12Ga0.88N by MOVPE. Journal of Crystal Growth, 2004, 272, 377-380. | 1.5 | 11 |
| 88 | Realization of extreme light extraction efficiency for mothâ€eye LEDs on SiC substrate using highâ€reflection electrode. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2180-2182. | 0.8 | 11 |
| 89 | Characterization of nonpolar a-plane GaN epi-layers grown on high-density patterned r-plane sapphire substrates. Journal of Crystal Growth, 2018, 484, 50-55. | 1.5 | 11 |
| 90 | Effects of Mg and Si doping in the guide layers of AlGaN-based ultraviolet-B band lasers. Journal of Crystal Growth, 2020, 535, 125537. | 1.5 | 11 |

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| 91 | Color-tunable emission in coaxial GaInN/GaN multiple quantum shells grown on three-dimensional nanostructures. Applied Surface Science, 2021, 539, 148279. | 6.1 | 11 |
| 92 | Enhanced Device Performance of GaInN-Based Green Light-Emitting Diode with Sputtered AlN Buffer Layer. Applied Sciences (Switzerland), 2019, 9, 788. | 2.5 | 10 |
| 93 | Thermodynamic analysis of GaInN-based light-emitting diodes operated by quasi-resonant optical excitation. Journal of Applied Physics, 2020, 128, . | 2.5 | 10 |
| 94 | Correlation between Optical and Structural Characteristics in Coaxial GaInN/GaN Multiple Quantum Shell Nanowires with AlGaN Spacers. ACS Applied Materials & Interfaces, 2020, 12, 51082-51091. | 8.0 | 10 |
| 95 | Analysis of carrier injection efficiency of AlGaN UV-B laser diodes based on the relationship between threshold current density and cavity length. Japanese Journal of Applied Physics, 2021, 60, 074002. | 1.5 | 10 |
| 96 | Structural and optical impacts of AlGaN undershells on coaxial GaInN/GaN multiple-quantum-shells nanowires. Nanophotonics, 2020, 9, 101-111. | 6.0 | 10 |
| 97 | In-plane GaN/AlGaN heterostructure fabricated by selective mass transport planar technology. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 139-142. | 3.5 | 9 |
| 98 | Relaxation of misfit-induced stress in nitride-based heterostructures. Journal of Crystal Growth, 2002, 237-239, 947-950. | 1.5 | 9 |
| 99 | Electrical properties of relaxed p-GaN/p-AlGaN superlattices and their application in ultraviolet-B light-emitting devices. Japanese Journal of Applied Physics, 2019, 58, SC1016. | 1.5 | 9 |
| 100 | Fabrication of vertical AlGaN-based deep-ultraviolet light-emitting diodes operating at high current density (â^¼43 kA cm<sup>â^'2</sup>) using a laser liftoff method. Applied Physics Express, 2022, 15, 041006. | 2.4 | 9 |
| 101 | Centimeter-scale laser lift-off of an AlGaN UVB laser diode structure grown on nano-patterned AlN. Applied Physics Express, 2022, 15, 051004. | 2.4 | 9 |
| 102 | Control of stress and crystalline quality in GaInN films used for green emitters. Journal of Crystal Growth, 2008, 310, 4920-4922. | 1.5 | 8 |
| 103 | In situ X-ray diffraction monitoring of GaInN/GaN superlattice during organometalic vapor phase epitaxy growth. Journal of Crystal Growth, 2014, 393, 108-113. | 1.5 | 8 |
| 104 | Annealing of the sputtered AlN buffer layer on râ€plane sapphire and its effect on aâ€plane GaN crystalline quality. Physica Status Solidi (B): Basic Research, 2017, 254, 1600723. | 1.5 | 8 |
| 105 | Tuning the Resonant Frequency of a Surface Plasmon by Double-Metallic Ag/Au Nanoparticles for High-Efficiency Green Light-Emitting Diodes. Applied Sciences (Switzerland), 2019, 9, 305. | 2.5 | 8 |
| 106 | Fabrication and Characterization of Multiquantum Shell Lightâ€Emitting Diodes with Tunnel Junction. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900774. | 1.8 | 8 |
| 107 | Emission characteristics of GaInN/GaN multiple quantum shell nanowire-based LEDs with different p-GaN growth conditions. Nanophotonics, 2021, 10, 3441-3450. | 6.0 | 8 |
| 108 | Effects of Mg dopant in Al-composition-graded Al<sub> x </sub>Ga<sub>1â^'x </sub>N (0.45Ââ‰Âx) on vertical electrical conductivity of ultrawide bandgap AlGaN pâ€“n junction. Applied Physics Express, 2021, 14, 096503. | 2.4 | 8 |

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| 109 | Study on the Seeded Growth of AlN Bulk Crystals by Sublimation. Japanese Journal of Applied Physics, 2004, 43, 7448-7453. | 1.5 | 7 |
| 110 | In situ X-ray diffraction monitoring during metalorganic vapor phase epitaxy growth of low-temperature-GaN buffer layer. Journal of Crystal Growth, 2012, 361, 1-4. | 1.5 | 7 |
| 111 | Efficiency Enhancement Mechanism of an Underlying Layer in GaInNâ€Based Green Lightâ€“Emitting Diodes. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900713. | 1.8 | 7 |
| 112 | Morphology Control and Crystalline Quality of p-Type GaN Shells Grown on Coaxial GaInN/GaN Multiple Quantum Shell Nanowires. ACS Applied Materials & Interfaces, 2021, 13, 54486-54496. | 8.0 | 7 |
| 113 | GaInNâ€based solar cells using GaInN/GaInN superlattices. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2463-2465. | 0.8 | 6 |
| 114 | Dislocation density dependence of stimulated emission characteristics in AlGaN/Al multiquantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1537-1540. | 0.8 | 6 |
| 115 | High quality Al<sub>0.99</sub>Ga<sub>0.01</sub>N layers on sapphire substrates grown at 1150 Â°C by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2017, 56, 015504. | 1.5 | 6 |
| 116 | Improvement of emission efficiency with a sputtered AlN buffer layer in GaInN-based green light-emitting diodes. Japanese Journal of Applied Physics, 2019, 58, SC1040. | 1.5 | 6 |
| 117 | MOVPE growth of n-GaN cap layer on GaInN/GaN multi-quantum shell LEDs. Journal of Crystal Growth, 2020, 539, 125571. | 1.5 | 6 |
| 118 | Room temperature pulsed operation of nitride nanowire-based multi-quantum shell laser diodes by MOVPE. Applied Physics Express, 2021, 14, 074004. | 2.4 | 6 |
| 119 | Performance of GaN-Based Semiconductor Laser with Spectral Broadening due to Compositional Inhomogeneity in GaInN Active Layer. Japanese Journal of Applied Physics, 2000, 39, 390-392. | 1.5 | 5 |
| 120 | Impact of H2-Preannealing of the Sapphire Substrate on the Crystallinity of Low-Temperature-Deposited AlN Buffer Layer. Japanese Journal of Applied Physics, 2005, 44, 3913-3917. | 1.5 | 5 |
| 121 | Homoepitaxial growth of AlN layers on freestanding AlN substrate by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2014, 390, 46-50. | 1.5 | 5 |
| 122 | Characterizations of GaN nanowires and GaInN/GaN multi-quantum shells grown by MOVPE. Japanese Journal of Applied Physics, 2020, 59, SGGE05. | 1.5 | 5 |
| 123 | Crystal Growth and Characterization of n-GaN in a Multiple Quantum Shell Nanowire-Based Light Emitter with a Tunnel Junction. ACS Applied Materials & Interfaces, 2021, 13, 37883-37892. | 8.0 | 5 |
| 124 | Nitrideâ€based heteroâ€fieldâ€effectâ€transistorâ€type photosensors with extremely high photosensitivity. Physica Status Solidi - Rapid Research Letters, 2013, 7, 215-217. | 2.4 | 4 |
| 125 | Optimization of indium tin oxide layer thickness for surface-plasmon-enhanced green light-emitting diodes. Japanese Journal of Applied Physics, 2019, 58, SCCC27. | 1.5 | 4 |
| 126 | Photoluminescence Characterization of Fluorescent Sic with High Boron and Nitrogen Concentrations. Materials Science Forum, 0, 1004, 265-271. | 0.3 | 4 |

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| 127 | Activation energy of Mg in a â€plane Ga<sub>1â€“x</sub>In<sub>x</sub> N (0 <) Tj ETQq1 1 0.784314 rgBT | 1.5 | 3 |
| 128 | Growth of thick GaInN on grooved (101Â¯1Â¯) GaN/(101Â¯2Â¯) 4H-SiC. Journal of Crystal Growth, 2009, 311, 2926-2928. | 1.5 | 3 |
| 129 | AlN and AlGaN by MOVPE for UV Light Emitting Devices. Materials Science Forum, 2008, 590, 175-210. | 0.3 | 2 |
| 130 | InGaN growth with various InN mole fractions on m-plane ZnO substrate by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2009, 311, 2929-2932. | 1.5 | 2 |
| 131 | Influence of trap level on an Al0.6Ga0.4N/Al0.5Ga0.5N metalâ€”semiconductorâ€”metal UV photodetector. Japanese Journal of Applied Physics, 2019, 58, SCCC26. | 1.5 | 2 |
| 132 | Improved Reverse Leakage Current in GaInN-Based LEDs With a Sputtered AlN Buffer Layer. IEEE Photonics Technology Letters, 2019, 31, 1971-1974. | 2.5 | 2 |
| 133 | In-situ curvature measurements of AlInN/GaN distributed Bragg reflectors during growths containing substrate temperature ramping steps. Journal of Crystal Growth, 2020, 531, 125357. | 1.5 | 2 |
| 134 | Space-charge effect on photogenerated-current and -voltage in III-nitride optoelectronic semiconductors. Photonics Research, 2021, 9, 1820. | 7.0 | 2 |
| 135 | Influence of silane flow rate on the structural and optical properties of GaN nanowires with multiple-quantum-shells. Journal of Crystal Growth, 2021, 570, 126201. | 1.5 | 2 |
| 136 | MOVPE growth of Si-doped GaN cap layers embedding GaN nanowires with multiple-quantum shells. Journal of Crystal Growth, 2022, 578, 126423. | 1.5 | 2 |
| 137 | Electrical Conductivity of Low-Temperature-Deposited Al0.1Ga0.9N Interlayer. Japanese Journal of Applied Physics, 2000, 39, 6493-6495. | 1.5 | 1 |
| 138 | Moth-Eye Light-Emitting Diodes. Materials Research Society Symposia Proceedings, 2004, 831, 19. | 0.1 | 1 |
| 139 | Control of p-type conduction in a-plane Ga1â^'xInxN (0<x<0.10) grown on r-plane sapphire substrate by metalorganic vapor-phase epitaxy. Journal of Crystal Growth, 2008, 310, 4996-4998. | 1.5 | 1 |
| 140 | Activation of Mg-Doped p-Type Al0.17Ga0.83N in Oxygen Ambient. Japanese Journal of Applied Physics, 2009, 48, 101002. | 1.5 | 1 |
| 141 | Defects in highly Mgâ€doped AlN. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1299-1301. | 1.8 | 1 |
| 142 | Demonstration of electron beam excitation laser using a GaInN-based multiquantum well active layer. Applied Physics Express, 2016, 9, 101001. | 2.4 | 1 |
| 143 | High photosensitivity AlGaN/GaInN/GaN heterojunction field-effect transistor type visible photosensors. Japanese Journal of Applied Physics, 2019, 58, SCCC22. | 1.5 | 1 |
| 144 | Optical and structural characterization of GaInN/GaN multiple quantum wells grown on nonpolar a-plane GaN templates by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2019, 58, SC1054. | 1.5 | 1 |

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